TEXAS INSTRUMENTS
SN74CB3Q3253
JAJSFN9C – OCTOBER 2003 – REVISED JUNE 2018

SN74CB3Q3253 デュアル1：4 FETマルチプレクサ/デマルチプレクサ、2.5V～3.3V低電圧高帯域バス・スイッチ

1 特長

- 高帯域データパス(最高500MHz)(1)
- デバイスの電源オン時とオフ時の両方で5V許容のI/O
- 動作範囲全体にわたって小さく平坦なオン抵抗(r_{on})特性(r_{on} = 4Ω、標準値)
- データI/Oポートのレール・ツー・レール・スイッチング
  - 3.3V V_{CC}で0～5Vのスイッチング
  - 2.5V V_{CC}で0～3.3Vのスイッチング
- 伝播遅延がゼロに近い双方向データ・フロー
- 低い入力/出力容量により負荷および信号歪みが最小化($C_{io(OFF)}$ = 3.5pF、標準値)
- 高いスイッチング周波数($f_{\overline{OE}}$ = 20MHz、最大値)
- データおよび制御入力にアンダーシュート・クランプ・ダイオードを搭載
- 低い消費電力(I_{CC} = 0.6mA、標準値)
- 2.3V～3.6Vの範囲のV_{CC}で動作
- データI/Oは0～5Vの信号レベルに対応(0.8V、1.2V、1.5V、1.8V、2.5V、3.3V、5V)
- 制御入力をTTLまたは5V/3.3V CMOS出力で駆動可能
- I_{off}により部分的パワーダウン・モードをサポート
- JESD 78, Class II準拠で100mA超のラッチアップ性能
- ESD性能はJESD 22に準拠しテスト済み
  - 人体モデルで2000V (A114-B、クラス II)
  - 荷電デバイス・モデルで1000V (C101)
- デジタルとアナログの両方のアプリケーションに対応: USBインターフェイス、差動信号インターフェイス・バス絶縁、低歪の信号ゲーティング

(1) CB3Qファミリの性能特性の詳細情報については、TIのアプリケーション・レポート『*CBT-C*、*CB3T*、*CB3Q信号スイッチ・ファミリ*』(SCDA008)を参照してください。

2 アプリケーション

- ビデオ放送: IPベースのマルチ・フォーマット・トランスコーダ
- ビデオ通信システム

3 概要

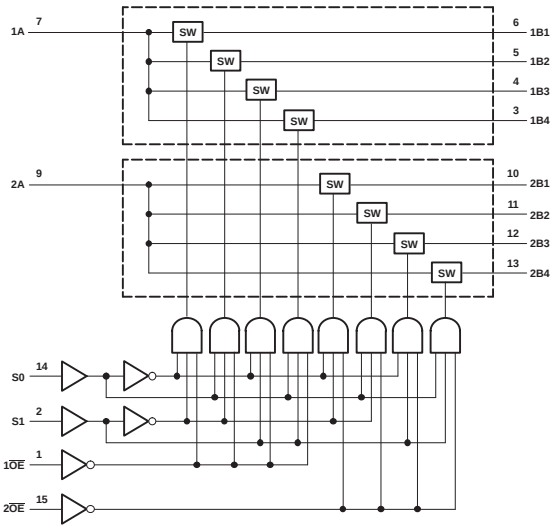
SN74CB3Q3253デバイスは高帯域のFETバス・スイッチで、チャージ・ポンプを使用してパス・トランジスタのゲート電圧を上昇させ、低い平坦なオン抵抗(r_{on})を実現します。オン抵抗が低く平坦であるため、伝搬遅延を最小限に抑えることができ、データ入出力(I/O)ポートでのレール・ツー・レール・スイッチングをサポートします。

製品情報

型番	パッケージ	本体サイズ(公称)
SN74CB3Q3253DBQ	SSOP (16)	4.90mm×3.90mm
SN74CB3Q3253DGV	TVSOP (16)	3.60mm×4.40mm
SN74CB3Q3253RGY	VQFN (16)	4.00mm×3.50mm
SN74CB3Q3253PW	TSSOP (16)	5.00mm×4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

ロジック図 (正論理)



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4 改訂履歴

Revision B (June 2015) から **Revision C** に変更 **Page**

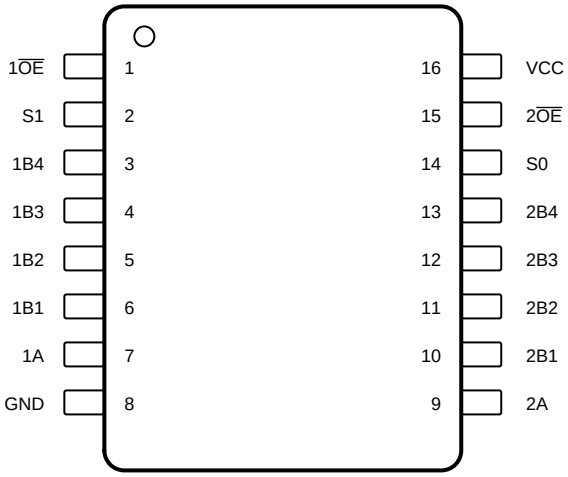
- Changed the pinout image appearance ... 3
- Updated the *Thermal Information* table ... 5

Revision A (November 2003) から **Revision B** に変更 **Page**

- 「*注文情報*」表を削除 ... 1
- 「*アプリケーション*」セクション、「*製品情報*」表、「*ピン構成および機能*」表、「*保管条件*」表、「*ESD定格*」表、「*機能説明*」セクション、「*デバイスの機能モード*」セクション、「*アプリケーションと実装*」セクション、「*電源に関する推奨事項*」セクション、「*レイアウト*」セクション、「*デバイスおよびドキュメントのサポート*」セクション、「*メカニカル、パッケージ、および注文情報*」セクションを追加 ... 1

5 Pin Configuration and Functions

DBQ, DGV, or PW Package
16-Pin SSOP, TVSOP, or TSSOP
Top View



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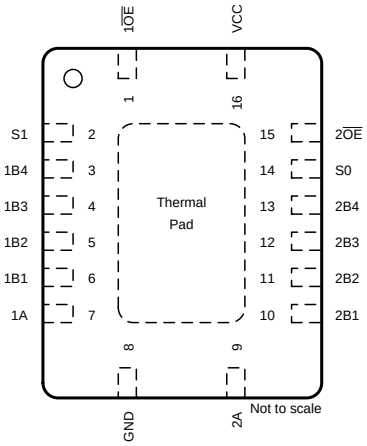
RGY Package
16-Pin VQFN
Top View



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Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
$1\overline{OE}$	1	I	Output Enable 1 Active-Low
S1	2	I	Select Pin 1
1B4	3	I/O	Channel 1 I/O 4
1B3	4	I/O	Channel 1 I/O 3
1B2	5	I/O	Channel 1 I/O 2
1B1	6	I/O	Channel 1 I/O 1
1A	7	I/O	Channel 1 common
GND	8	—	Ground
2A	9	I/O	Channel 2 common
2B1	10	I/O	Channel 2 I/O 1
2B2	11	I/O	Channel 2 I/O 2
2B3	12	I/O	Channel 2 I/O 3
2B4	13	I/O	Channel 2 I/O 4
S0	14	I	Select Pin 0
$2\overline{OE}$	15	I	Output Enable 2 Active-Low
V_{CC}	16	—	Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	4.6	V
V_{IN}	Control input voltage(2)(3)		–0.5	7	V
$V_{I/O}$	Switch I/O voltage(2)(3)(4)		–0.5	7	V
I_{IK}	Control input clamp current	V_{IN} < 0		–50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O}$ < 0		–50	mA
$I_{I/O}$	ON-state switch current(5)			±64	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground, unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) V_I and V_O are used to denote specific conditions for $V_{I/O}$.
(5) I_I and I_O are used to denote specific conditions for $I_{I/O}$.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	+2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	+1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3 V to 2.7 V	1.7	5.5	V
		V_{CC} = 2.7 V to 3.6 V	2	5.5	
V_{IL}	Low-level control input voltage	V_{CC} = 2.3 V to 2.7 V	0	0.7	V
		V_{CC} = 2.7 V to 3.6 V	0	0.8	
$V_{I/O}$	Data input/output voltage		0	5.5	V
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, (SCBA004).

6.4 Thermal Information

THERMAL METRIC(1)		SN74CB3Q3253				UNIT
		DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	114.3	126	112.7	45.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	65.4	51.3	47.5	59.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	56.8	57.8	57.85	23.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	18.3	5.9	6	2.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	56.4	57.3	57.3	23.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	11.5	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS			MIN	TYP(2)	MAX	UNIT
V_{IK}		V_{CC} = 3.6 V,	I_I = –18 mA				–1.8	V
I_{IN}	Control inputs	V_{CC} = 3.6 V,	V_{IN} = 0 to 5.5 V				±1	µA
I_{OZ}(3)		V_{CC} = 3.6 V,	V_O = 0 to 5.5 V, V_I = 0,	Switch OFF, V_{IN} = V_{CC} or GND			±1	µA
I_{off}		V_{CC} = 0,	V_O = 0 to 5.5 V,	V_I = 0			1	µA
I_{CC}		V_{CC} = 3.6 V,	$I_{I/O}$ = 0, Switch ON or OFF,	V_{IN} = V_{CC} or GND		0.6	2	mA
ΔI_{CC}(4)	Control inputs	V_{CC} = 3.6 V,	One input at 3 V,	Other inputs at V_{CC} or GND			30	µA
I_{CCD}(5)	Per control input	V_{CC} = 3.6 V,	A and B ports open,	$\overline{OE}$ input		0.15	0.16	mA/ MHz
		Control input switching at 50% duty cycle		S input		0.04	0.05	
C_{in}	Control inputs	V_{CC} = 3.3 V,	V_{IN} = 5.5 V, 3.3 V, or 0			2.5	3.5	pF
$C_{io(OFF)}$	A port	V_{CC} = 3.3 V,	Switch OFF, V_{IN} = V_{CC} or GND,	$V_{I/O}$ = 5.5 V, 3.3 V, or 0		8	11	pF
	B port	V_{CC} = 3.3 V,	Switch OFF, V_{IN} = V_{CC} or GND,	$V_{I/O}$ = 5.5 V, 3.3 V, or 0		3.5	4.5	pF
$C_{io(ON)}$		V_{CC} = 3.3 V,	Switch ON, V_{IN} = V_{CC} or GND,	$V_{I/O}$ = 5.5 V, 3.3 V, or 0		13	17	pF
r_{on}(6)		V_{CC} = 2.3 V, TYP at V_{CC} = 2.5 V	V_I = 0,	I_O = 30 mA		4	10	Ω
			V_I = 1.7 V,	I_O = –15 mA		4.5	11	
		V_{CC} = 3 V	V_I = 0,	I_O = 30 mA		3.5	8	
			V_I = 2.4 V,	I_O = –15 mA		4	10	

(1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Figure 2).
(6) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
$f_{\overline{OE}}$ or f_S (1)	$\overline{OE}$ or S	A or B		10		20	MHz
t_{pd} (2)	A or B	B or A		0.12		0.18	ns
$t_{pd(s)}$	S	A	1.5	6.7	1.5	5.9	ns
t_{en}	S	B	1.5	6.7	1.5	5.9	ns
	$\overline{OE}$	A or B	1.5	6.7	1.5	5.9	
t_{dis}	S	B	1	6.1	1	6.1	ns
	$\overline{OE}$	A or B	1	6.1	1	6.1	

(1) Maximum switching frequency for control input ($V_O > V_{CC}$, V_I = 5 V, $R_L \geq 1$ MΩ, C_L = 0).
(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

6.7 Typical Characteristics

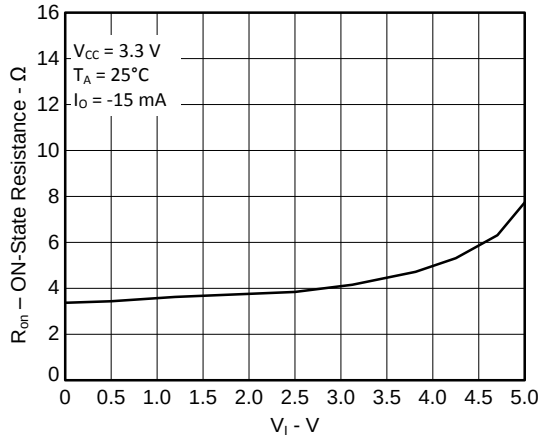


Figure 1. Typical r_{on} vs V_I, V_{CC} = 3.3 V and I_O = –15 mA

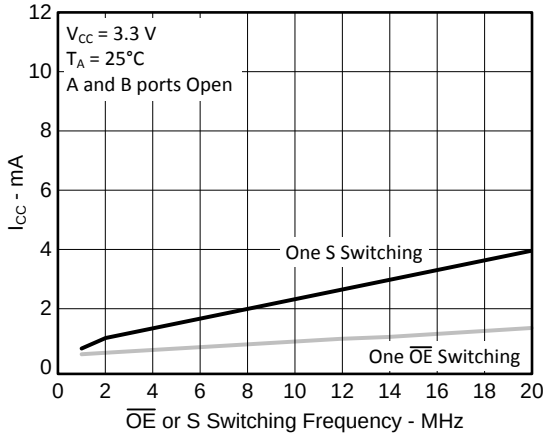
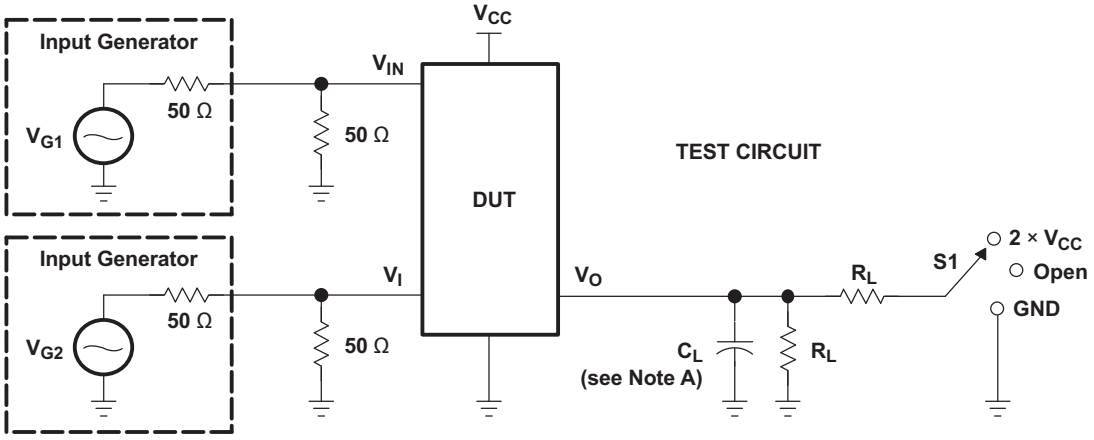
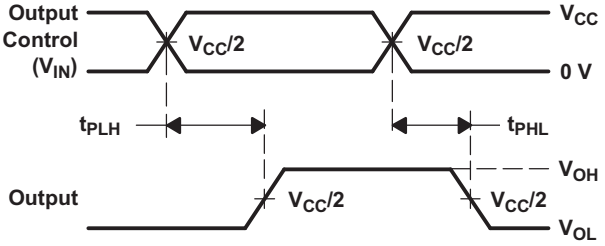


Figure 2. Typical I_{CC} vs $\overline{OE}$ or S Switching Frequency, V_{CC} = 3.3 V

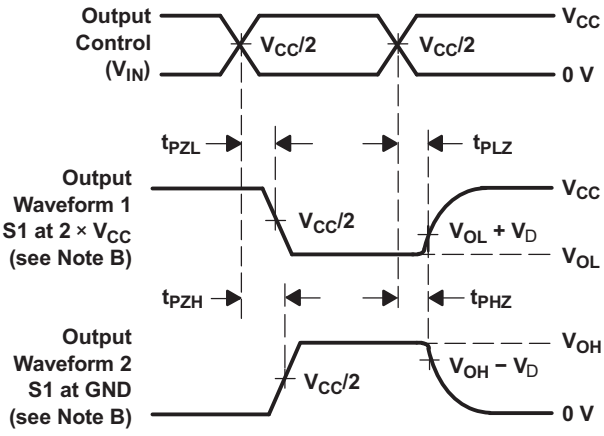
7 Parameter Measurement Information



TEST	V_{CC}	S1	R_L	V_I	C_L	V_Δ
$t_{pd(s)}$	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	V_{CC} or GND V_{CC} or GND	30 pF 50 pF	
t_{PLZ}/t_{PZL}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	2 × V_{CC} 2 × V_{CC}	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.3 V
t_{PHZ}/t_{PZH}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	GND GND	500 Ω 500 Ω	V_{CC} V_{CC}	30 pF 50 pF	0.15 V 0.3 V



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES ($t_{pd(s)}$)



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as $t_{pd(s)}$. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

8 Detailed Description

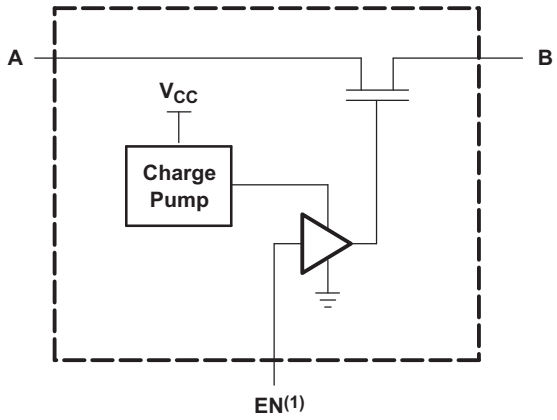
8.1 Overview

The SN74CB3Q3253 device is a high-bandwidth FET bus switch using a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3253 device provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

The SN74CB3Q3253 device is organized as two 1-of-4 multiplexers/demultiplexers with separate output-enable ($1\overline{OE}$, $2\overline{OE}$) inputs. The select (S0, S1) inputs control the data path of each multiplexer/demultiplexer. When $\overline{OE}$ is low, the associated multiplexer/demultiplexer is enabled, and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{OE}$ is high, the associated multiplexer/demultiplexer is disabled, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

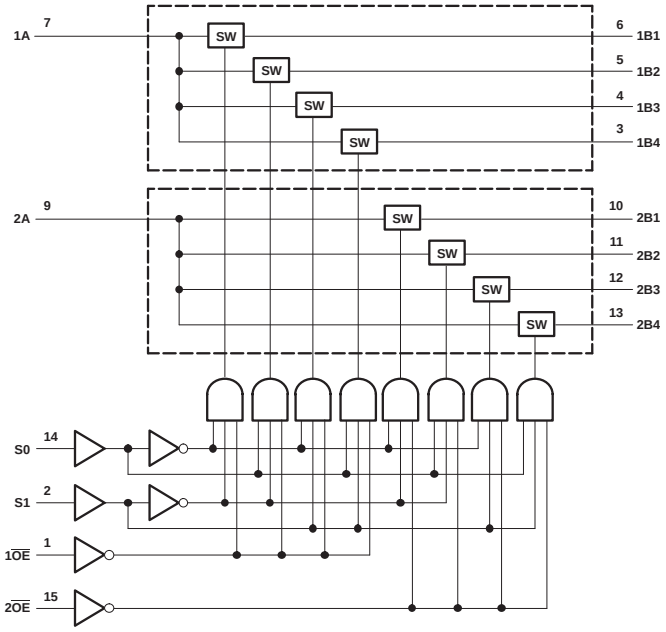
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



(1) EN is the internal enable signal applied to the switch.

Figure 4. Simplified Schematic, Each FET Switch (SW)

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CB3Q3253 device has a high-bandwidth data path (up to 500 MHz) and has 5-V tolerant I/Os with the device powered up or powered down. It also has low and flat ON-state resistance (r_{on}) characteristics over operating range (r_{on} = 4 Ω Typical)

This device also has rail-to-rail switching on data I/O ports for 0- to 5-V switching with 3.3-V $V_{CC}$and 0- to 3.3-V switching with 2.5-V V_{CC}as well as bidirectional data flow with near-zero propagation delay and low input and output capacitance that minimizes loading and signal distortion ($C_{io(OFF)}$ = 3.5 pF Typical)

The SN74CB3Q3253 also provides a fast switching frequency ($f_{\overline{OE}}$ = 20 MHz Maximum) with data and control inputs that provide undershoot clamp diodes as well as low power consumption (I_{CC} = 0.6 mA Typical)

The V_{CC} operating range is from 2.3 V to 3.6 V and the data I/Os support 0- to 5-V signal levels of (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)

The control inputs can be driven by TTL or 5-V and 3.3-V CMOS outputs as well as I_{off} Supports Partial-Power-Down Mode Operation

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74CB3Q3253.

Table 1. Function Table
(Each Multiplexer/Demultiplexer)

INPUTS			INPUT/OUTPUT	FUNCTION
$\overline{OE}$	S1	S0	A	
L	L	L	B1	A port = B1 port
L	L	H	B2	A port = B2 port
L	H	L	B3	A port = B3 port
L	H	H	B4	A port = B4 port
H	X	X	Z	Disconnect

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CB3Q3253 device can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration.

9.2 Typical Application

The application shown here is a 4-bit bus being multiplexed between two devices. the $\overline{OE}$ and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

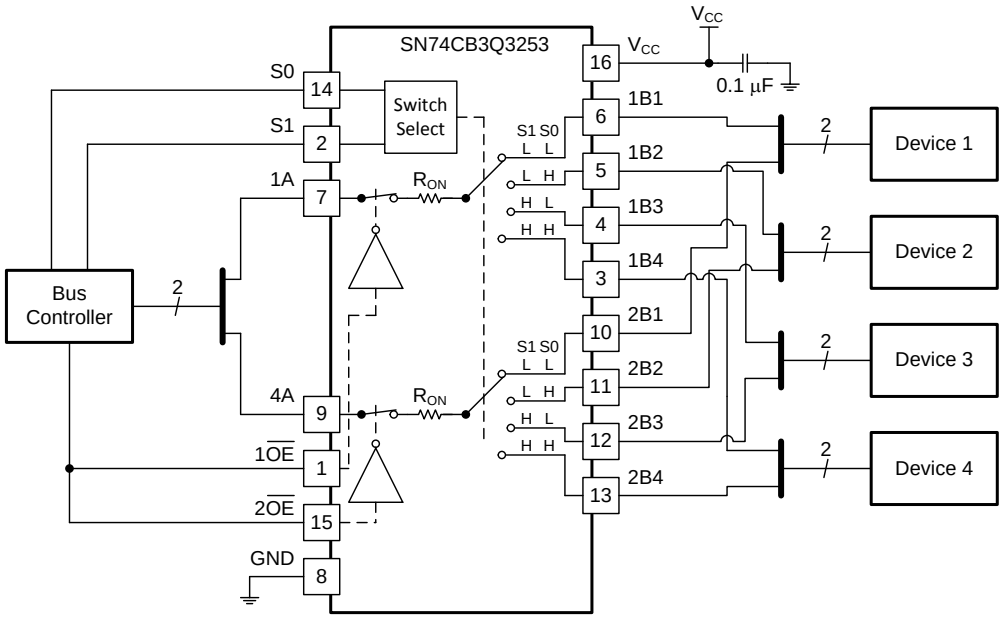


Figure 5. Typical Application of the SN74CB3Q3253

9.2.1 Design Requirements

The 0.1-µF capacitor should be place as close as possible to the device.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
   - For specified high and low levels, see V_{IH} and V_{IL} in *Recommended Operating Conditions*.
   - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V_{CC}.
2. Recommended Output Conditions:
   - Load currents should not exceed ±128 mA per channel.
3. Frequency Selection Criterion:
   - Maximum frequency tested is 500 MHz.
   - Added trace resistance and capacitance can reduce maximum frequency capability; use layout practices as directed in *Layout*.

Typical Application (continued)

9.2.3 Application Curve

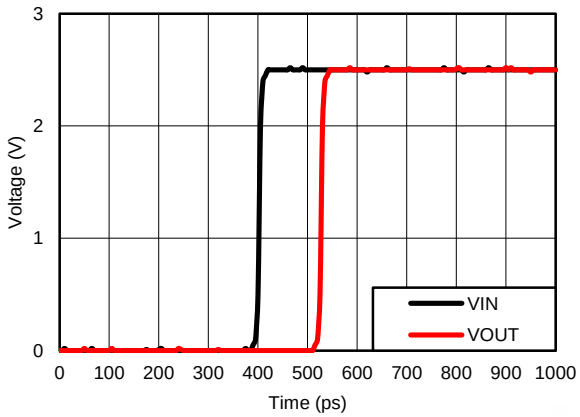


Figure 6. Propagation Delay (t_{pd}) Simulation Result at V_{CC} = 2.5 V

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Absolute Maximum Ratings* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF bypass capacitor is recommended. If multiple pins are labeled V_{CC}, then a 0.01-μF or 0.022-μF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD}, a 0.1-μF bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 7 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

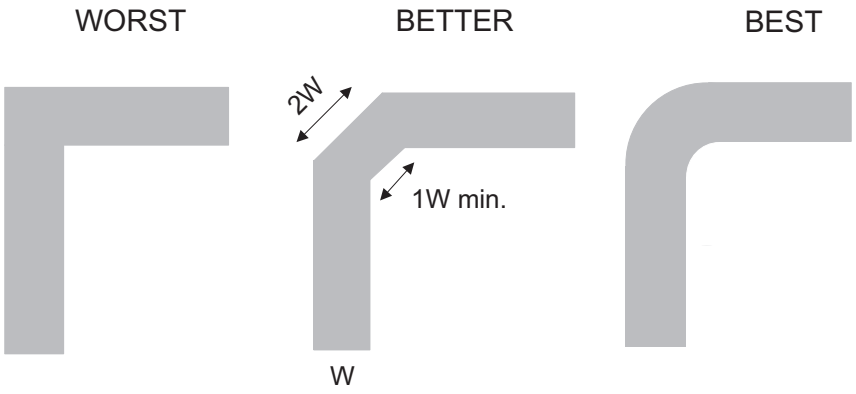


Figure 7. Trace Example

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

- *『低速またはフローティングCMOS入力の影響』*、SCBA004
- *『テキサス・インスツルメンツ製信号スイッチの的確な選択』*、SZZA030

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™オンライン・コミュニティ ***TIのE2E（Engineer-to-Engineer）コミュニティ。エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイディアを検討して、問題解決に役立てることができます。***

設計サポート ***TIの設計サポート*** **役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。**

12.4 商標

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静電気放電に関する注意事項

これらのデバイスは、限定的なESD（静電破壊）保護機能を内 蔵しています。保存時または取り扱い時は、MOSゲートに対す る静電破壊を防止するために、リード線同士をショートさせて おくか、デバイスを導電フォームに入れる必要があります。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74CB3Q3253DBQR	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.B	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.A	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.B	Active	Production	SSOP (DBQ) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DGVR	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVR.B	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVRG4	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVRG4.B	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PW	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	-40 to 85	BU253
SN74CB3Q3253PWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.B	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253RGYR	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.B	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.B	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

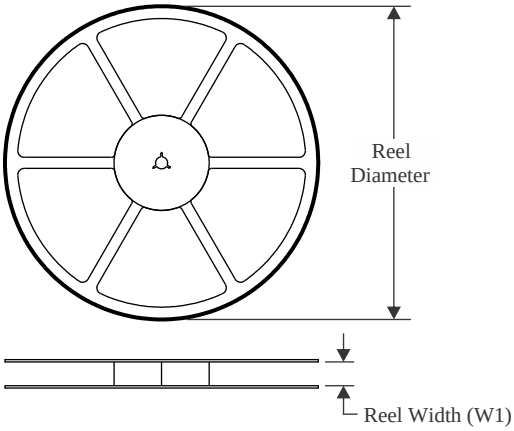
(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

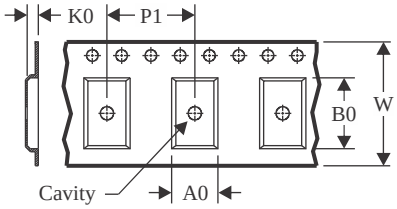
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

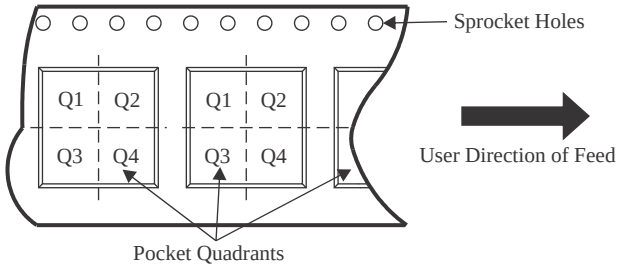


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

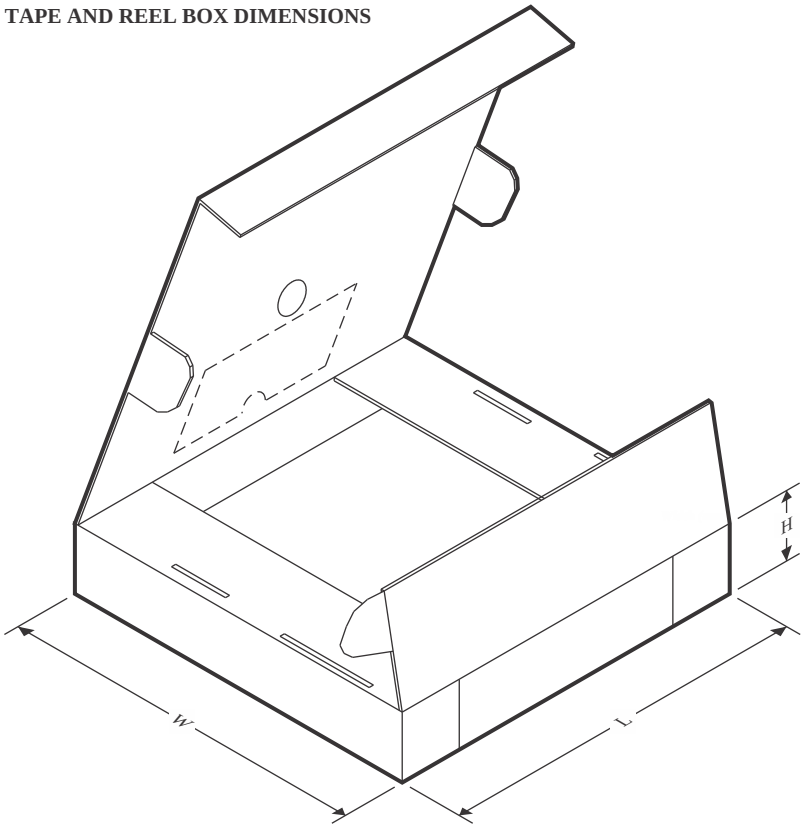
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3253DBQRG4	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3253DGVRG4	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3253PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74CB3Q3253RGYRG4	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

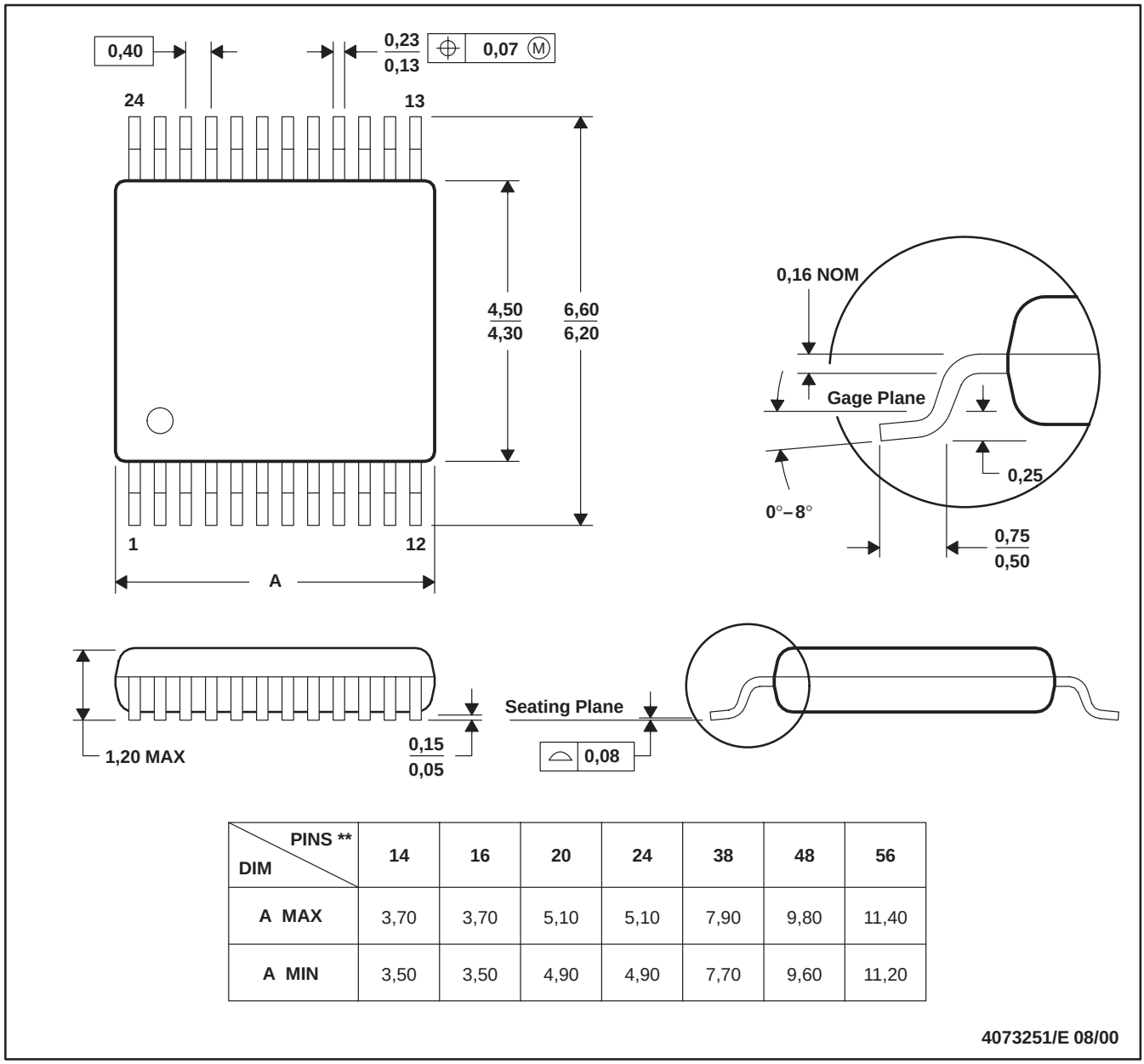


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CB3Q3253DBQRG4	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74CB3Q3253DGVRG4	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74CB3Q3253PWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	353.0	353.0	32.0
SN74CB3Q3253RGYRG4	VQFN	RGY	16	3000	353.0	353.0	32.0

DGV (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

24 PINS SHOWN



DIM \ PINS **	14	16	20	24	38	48	56
A MAX	3,70	3,70	5,10	5,10	7,90	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	7,70	9,60	11,20

4073251/E 08/00

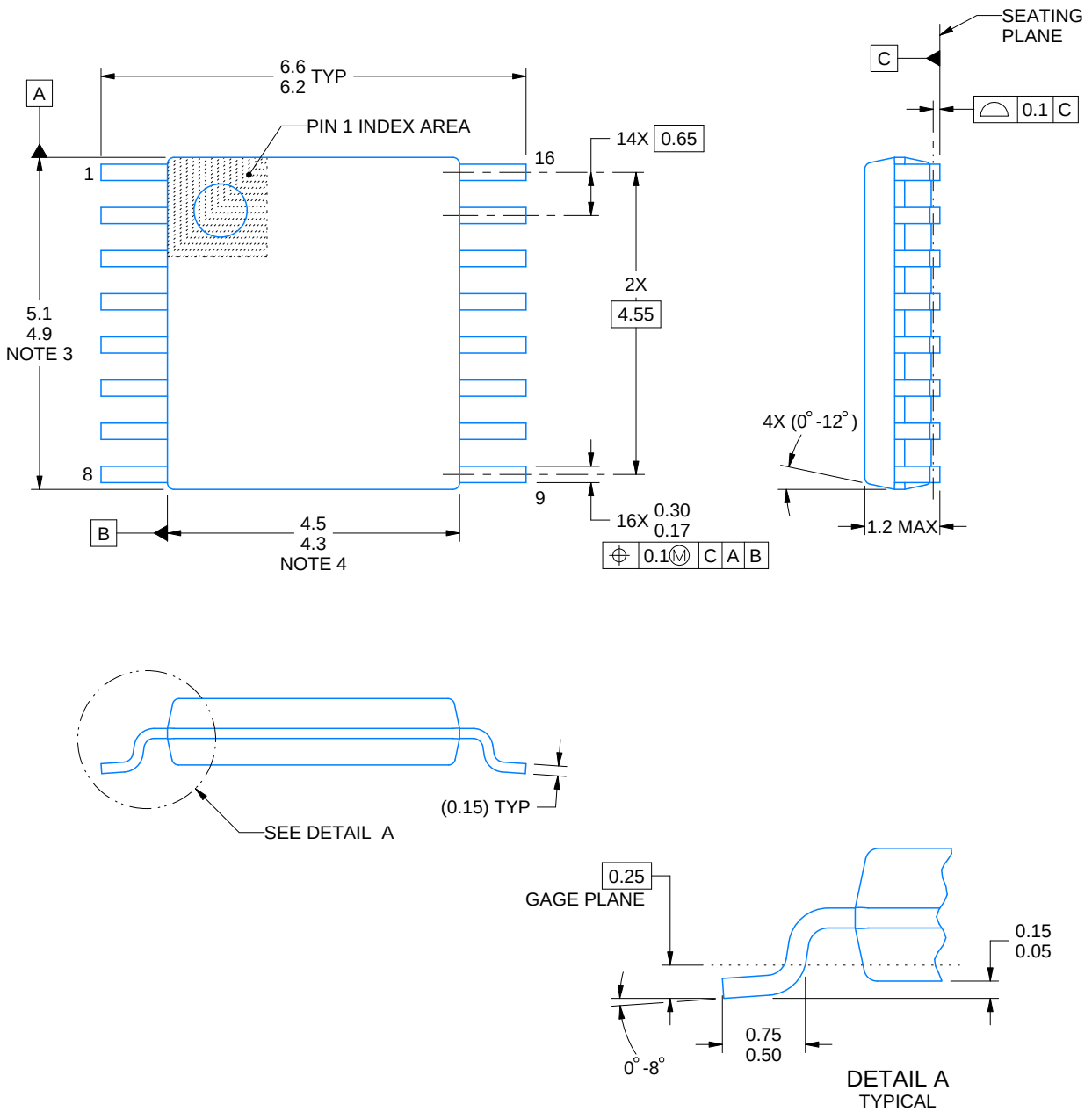
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: 24/48 Pins – MO-153
14/16/20/56 Pins – MO-194

PACKAGE OUTLINE

PW0016A

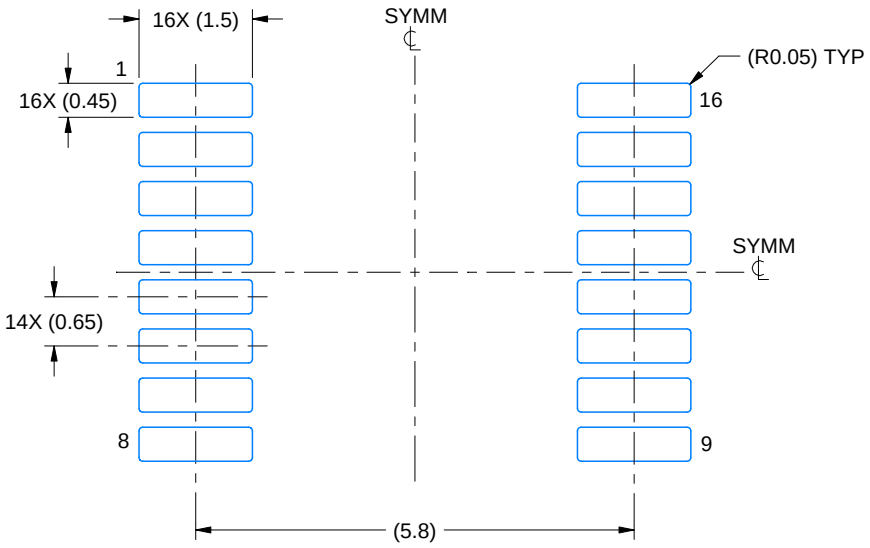
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



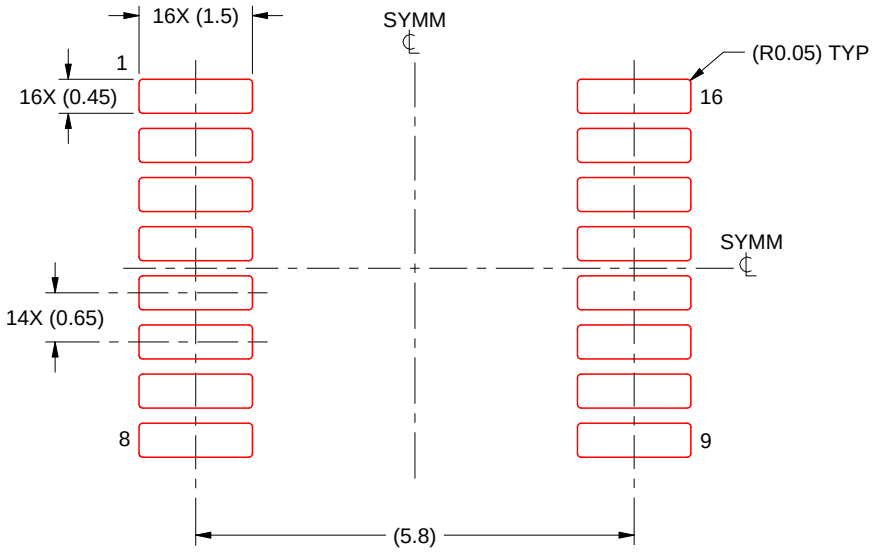
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

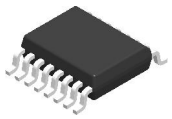


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

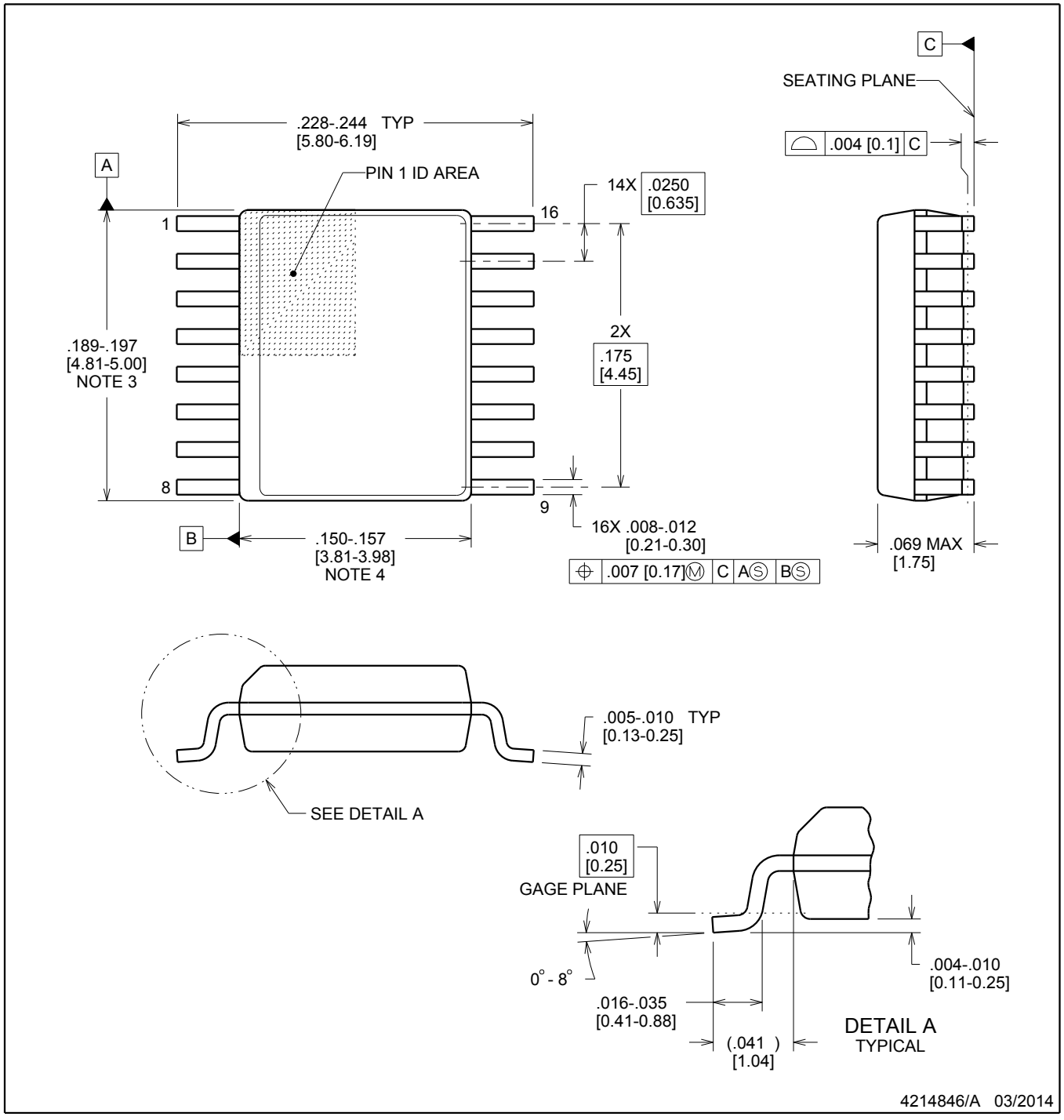


PACKAGE OUTLINE

DBQ0016A

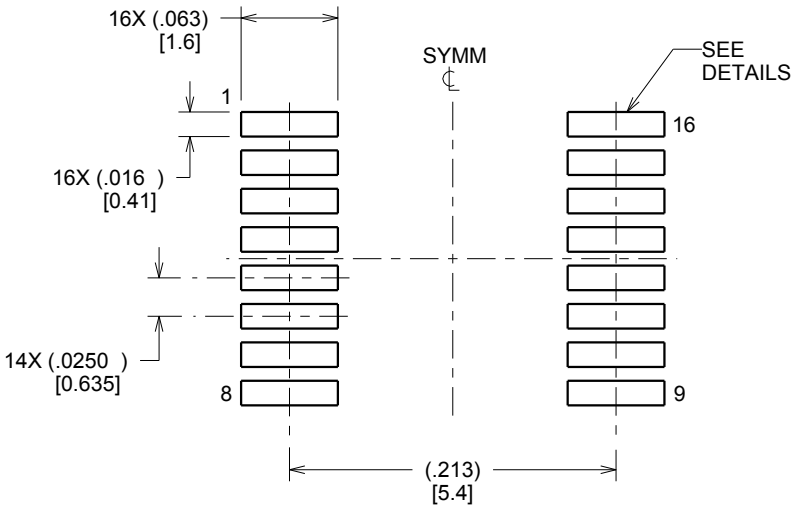
SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE

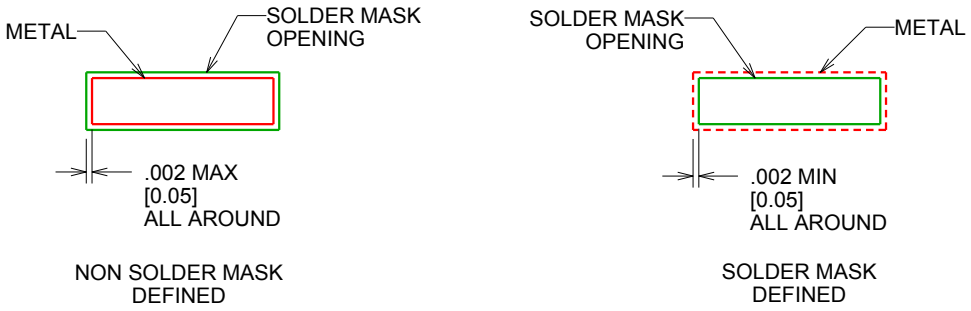


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

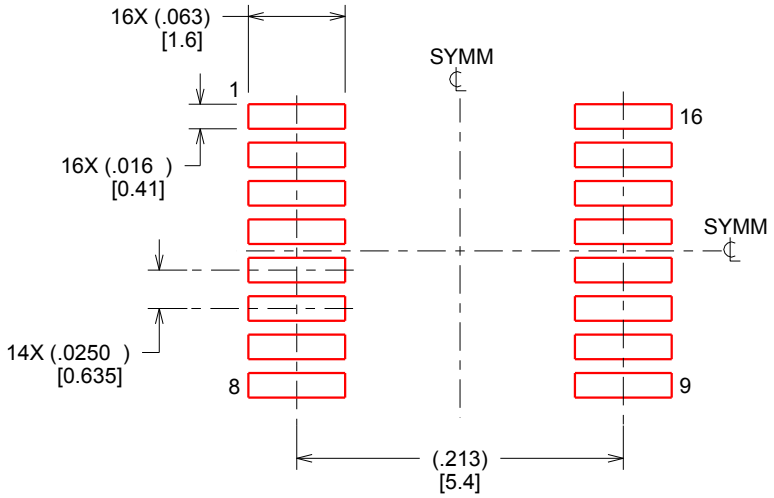
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



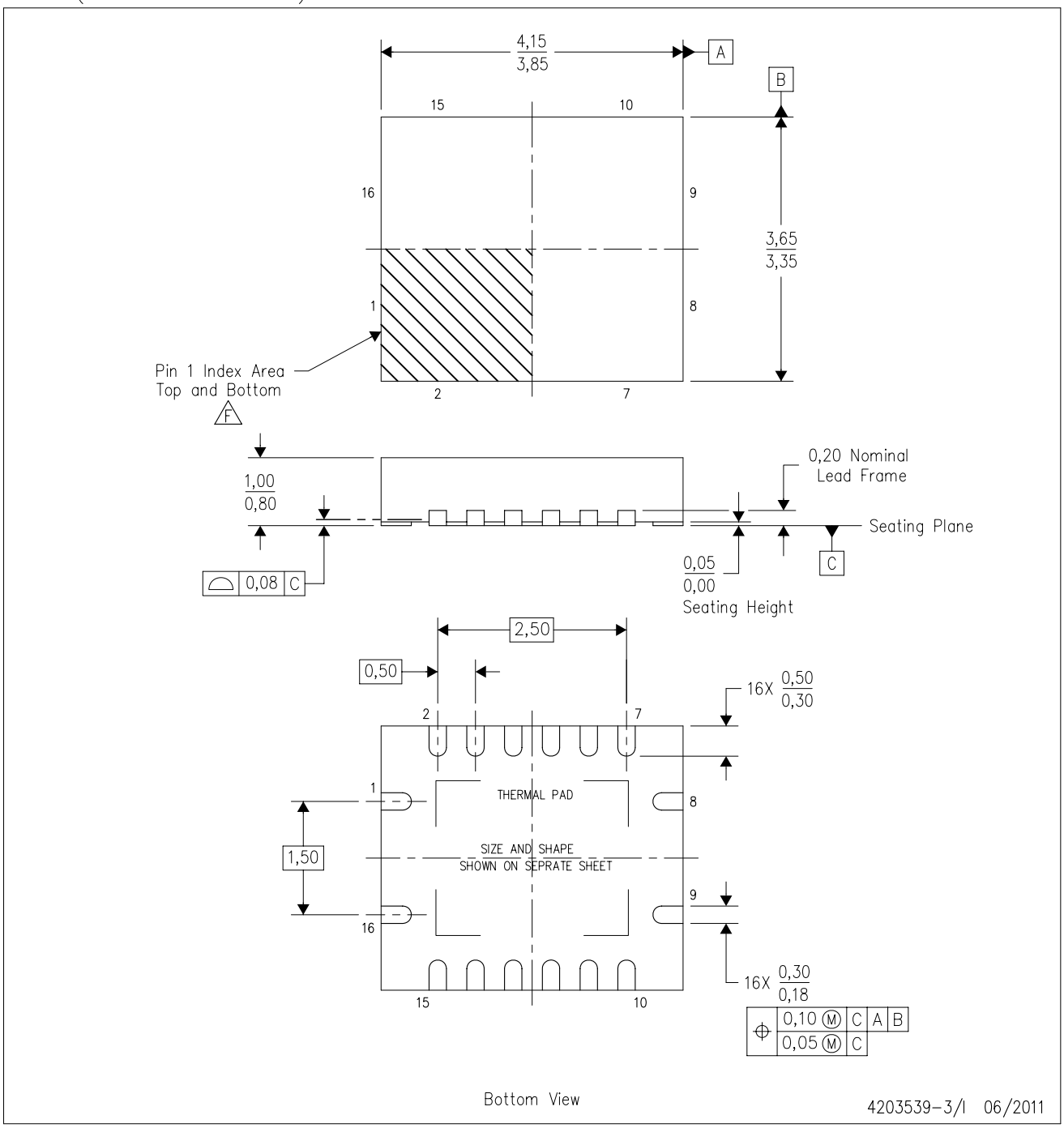
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No–Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
G. Package complies to JEDEC MO–241 variation BA.

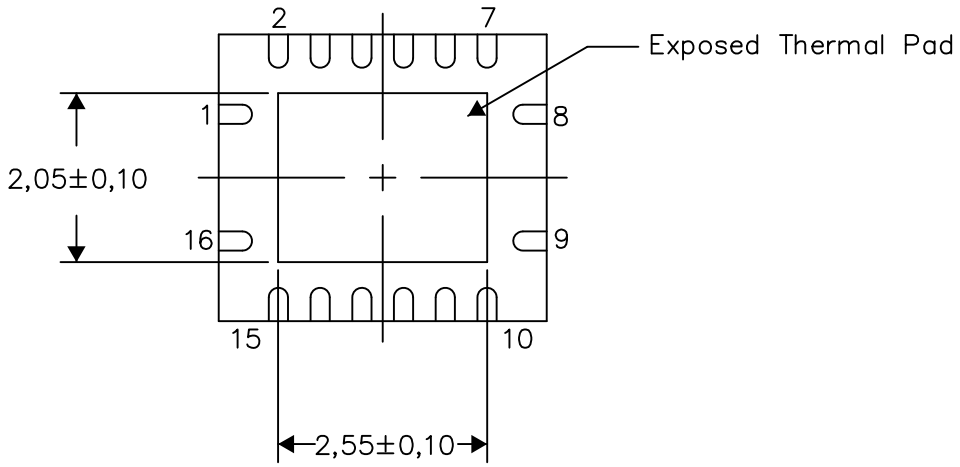
RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



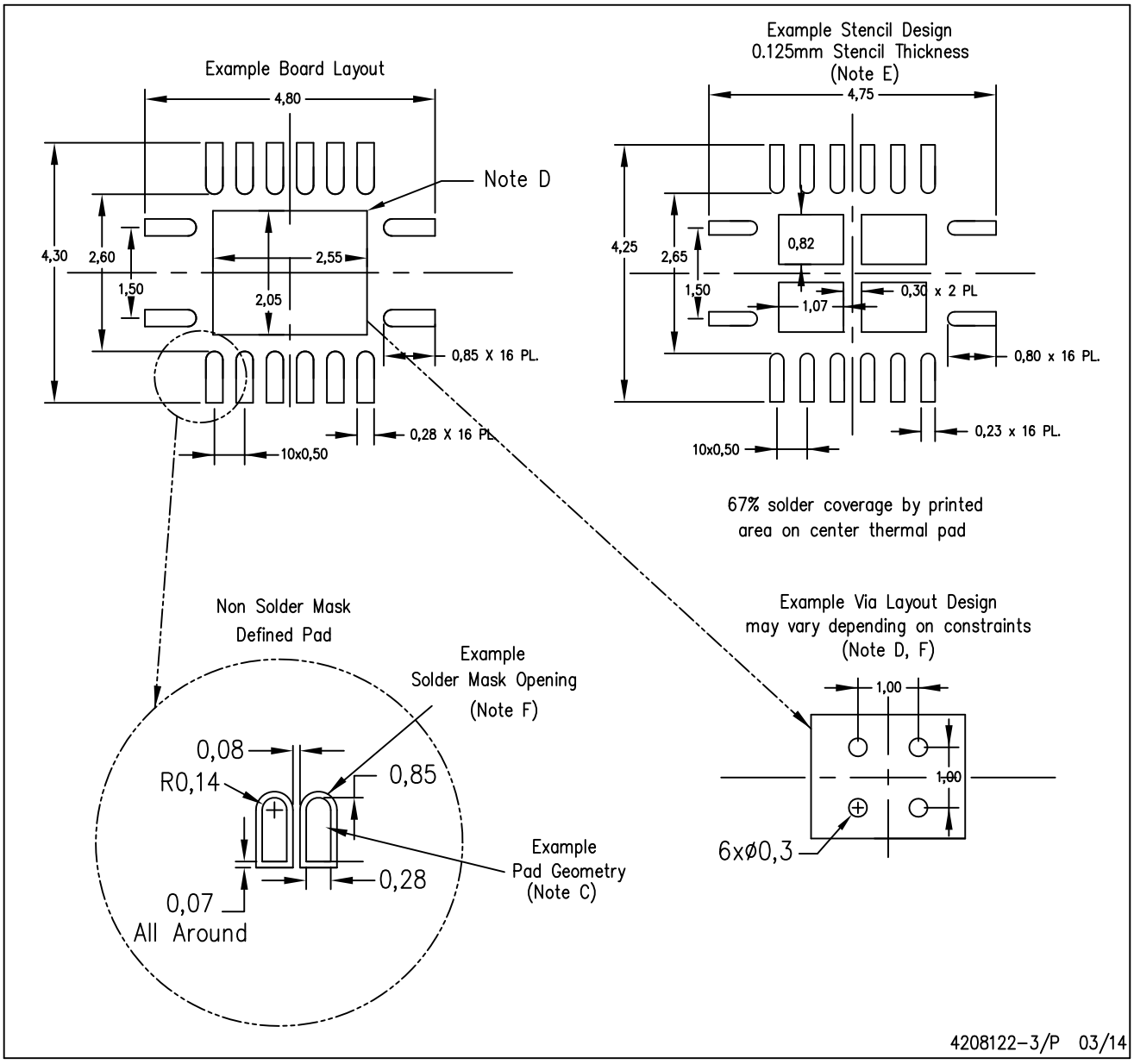
Bottom View

Exposed Thermal Pad Dimensions

4206353–3/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat–Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

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